NTD4805N, NVD4805N

MOSFET – Power, Single, N-Channel, DPAK/IPAK
30 V, 88 A

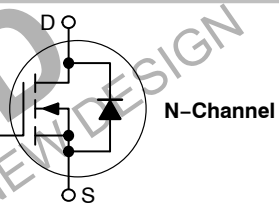
ON Semiconductor®

http://onsemi.com

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	5.0 mΩ @ 10 V	88 A
	7.4 mΩ @ 4.5 V	

Features
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- NVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free and are RoHS Compliant

Applications
- CPU Power Delivery
- DC−DC Converters
- Low Side Switching

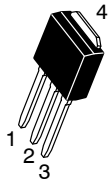


MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	30	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current ($R_{\theta JA}$) (Note 1)	Steady State	T_A = 25°C	I_D	17.4	A
		T_A = 85°C		13.5	
Power Dissipation ($R_{\theta JA}$) (Note 1)		T_A = 25°C	P_D	2.65	W
Continuous Drain Current ($R_{\theta JA}$) (Note 2)		T_A = 25°C	I_D	12.7	A
		T_A = 85°C		9.8	
Power Dissipation ($R_{\theta JA}$) (Note 2)		T_A = 25°C	P_D	1.41	W
Continuous Drain Current ($R_{\theta JC}$) (Note 1)		T_C = 25°C	I_D	95	A
		T_C = 85°C		73	
Power Dissipation ($R_{\theta JC}$) (Note 1)		T_C = 25°C	P_D	79	W
Pulsed Drain Current	t_p=10μs	T_A = 25°C	I_{DM}	175	A
Current Limited by Package		T_A = 25°C	$I_{DmaxPkg}$	45	A
Operating Junction and Storage Temperature			T_J, T_{stg}	−55 to 175	°C
Source Current (Body Diode)			I_S	55	A
Source Current (Body Diode) Pulsed t_p=20 μs			I_{SM}	175	A
Drain to Source dV/dt			dV/dt	6.0	V/ns
Single Pulse Drain−to−Source Avalanche Energy (V_{DD} = 24 V, V_{GS} = 10 V, L = 1.0 mH, $I_{L(pk)}$ = 24 A, R_G = 25 Ω)			E_{AS}	288	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

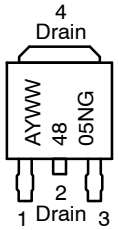
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

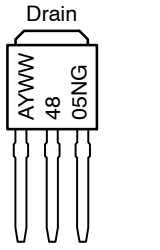
DPAK
CASE 369AA
(Bent Lead)
STYLE 2



IPAK
CASE 369D
(Straight Lead DPAK)
STYLE 2

MARKING DIAGRAMS & PIN ASSIGNMENTS





A = Assembly Location*
Y = Year
WW = Work Week
4805N = Device Code
G = Pb−Free Package

* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

ORDERING INFORMATION
See detailed ordering and shipping information on page 6 of this data sheet.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case (Drain)	$R_{\theta JC}$	1.9	°C/W
Junction−to−TAB (Drain)	$R_{\theta JC-TAB}$	3.5	
Junction−to−Ambient − Steady State (Note 1)	$R_{\theta JA}$	56.6	
Junction−to−Ambient − Steady State (Note 2)	$R_{\theta JA}$	106.6	

1. Surface−mounted on FR4 board using 1 in sq pad size, 1 oz Cu.
2. Surface−mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		30			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				27		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 24 V	T_J = 25°C			1.0	μA
			T_J = 125°C			10	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.5		2.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				5.86		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 to 11.5 V	I_D = 30 A		4.3	5.0	mΩ
			I_D = 15 A		4.2		
		V_{GS} = 4.5 V	I_D = 30 A		6.0	7.4	
			I_D = 15 A		5.8		
Forward Transconductance	g_{FS}	V_{DS} = 15 V, I_D = 15 A			17		S
CHARGES AND CAPACITANCES							
Input Capacitance	C_{iss}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 12 V			2865		pF
Output Capacitance	C_{oss}				610		
Reverse Transfer Capacitance	C_{rss}				338		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 30 A			20.5	26	nC
Threshold Gate Charge	$Q_{G(TH)}$				4.05		
Gate−to−Source Charge	Q_{GS}				8.28		
Gate−to−Drain Charge	Q_{GD}				8.36		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 11.5 V, V_{DS} = 15 V, I_D = 30 A			48		nC
SWITCHING CHARACTERISTICS (Note 4)							
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 15 A, R_G = 3.0 Ω			17.2		ns
Rise Time	t_r				20.3		
Turn−Off Delay Time	$t_{d(off)}$				20.8		
Fall Time	t_f				8.0		
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 11.5 V, V_{DS} = 15 V, I_D = 15 A, R_G = 3.0 Ω			10.8		ns
Rise Time	t_r				20.5		
Turn−Off Delay Time	$t_{d(off)}$				30.8		
Fall Time	t_f				4.4		

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted) (continued)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 30 A	T_J = 25°C		0.87	1.2	V
			T_J = 125°C		0.76		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dIs/dt = 100 A/μs, I_S = 30 A			25.7		ns
Charge Time	ta				13.1		
Discharge Time	tb				12.6		
Reverse Recovery Time	Q_{RR}				18		nC
PACKAGE PARASITIC VALUES							
Source Inductance	L_S	T_A = 25°C			2.49		nH
Drain Inductance, DPAK	L_D				0.0164		
Drain Inductance, IPAK	L_D				1.88		
Gate Inductance	L_G				3.46		
Gate Resistance	R_G				0.8		Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
4. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

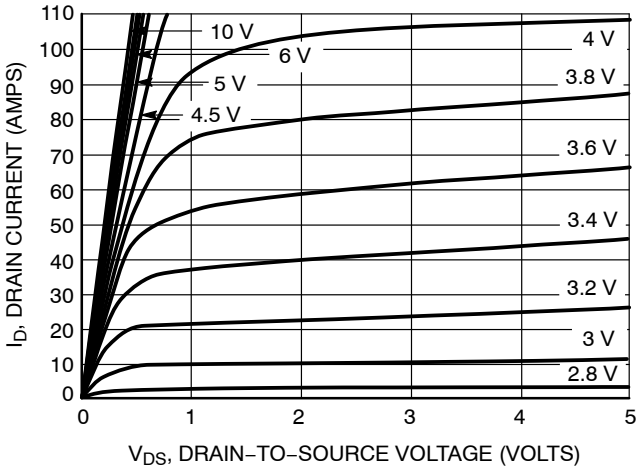


Figure 1. On−Region Characteristics

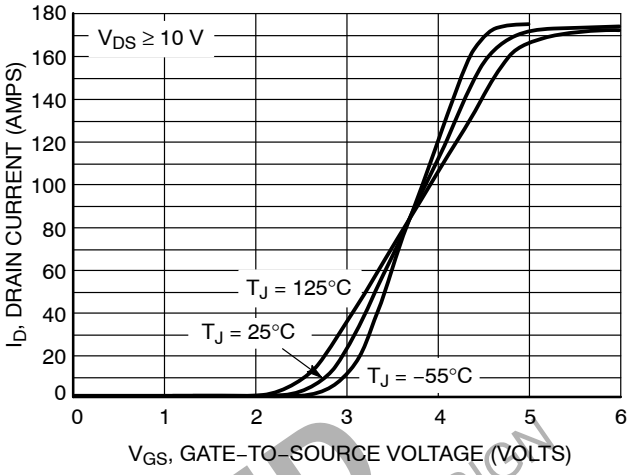


Figure 2. Transfer Characteristics

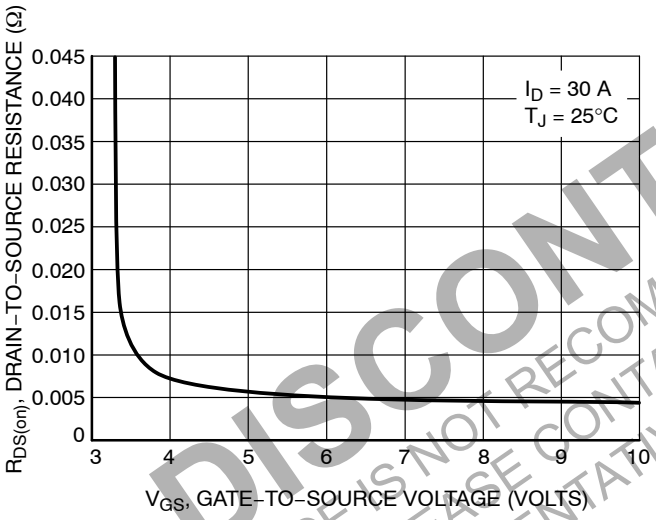


Figure 3. On−Resistance vs. Gate−to−Source Voltage

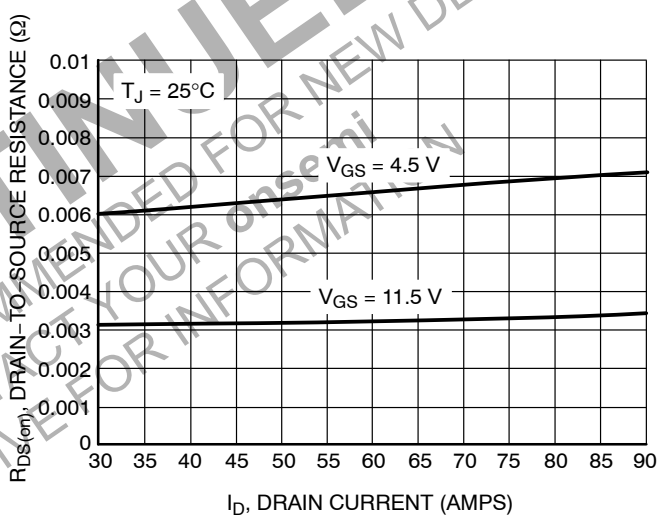


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

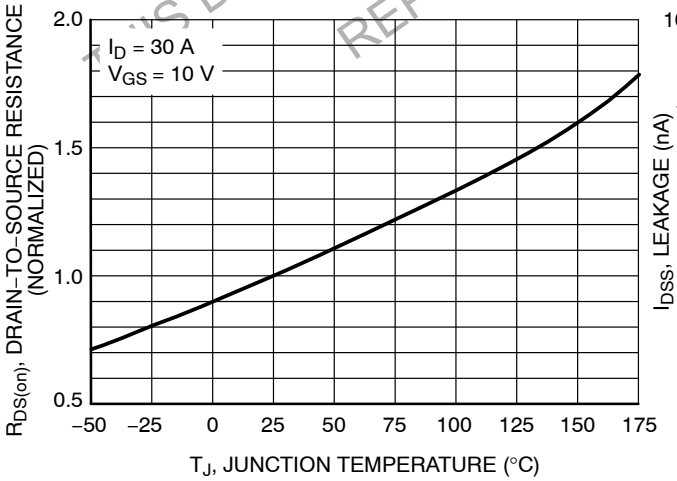


Figure 5. On−Resistance Variation with Temperature

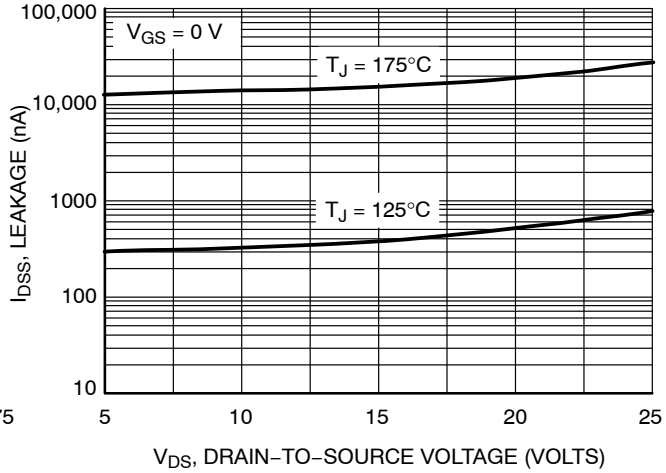


Figure 6. Drain−to−Source Leakage Current vs. Drain Voltage

TYPICAL PERFORMANCE CURVES

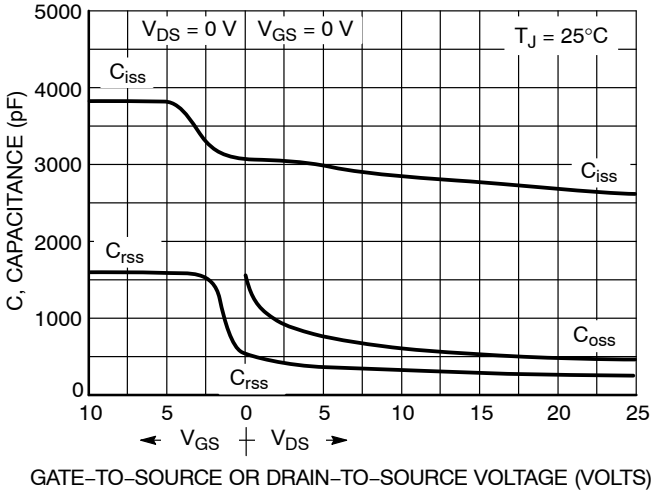


Figure 7. Capacitance Variation

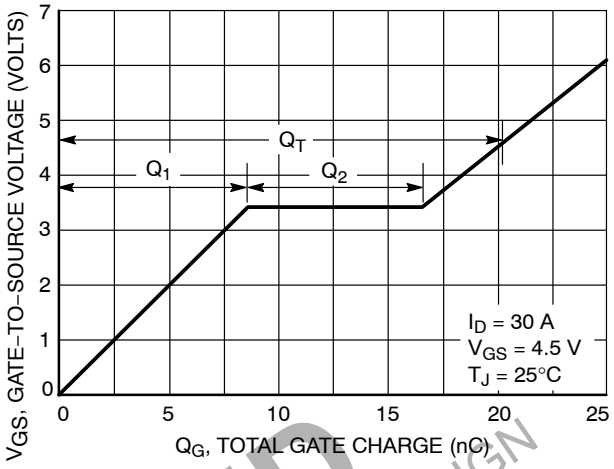


Figure 8. Gate–To–Source and Drain–To–Source Voltage vs. Total Charge

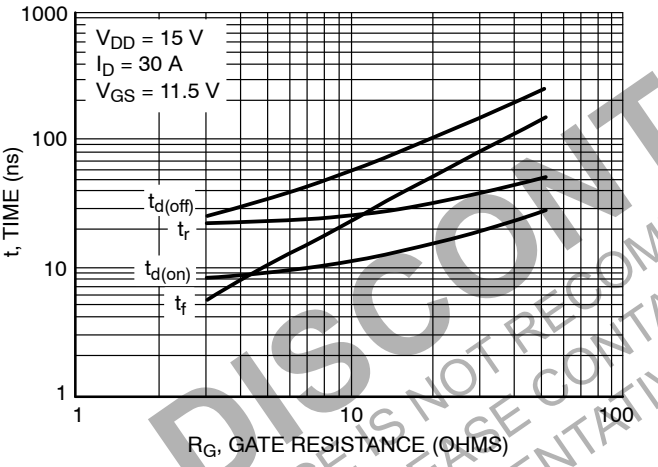


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

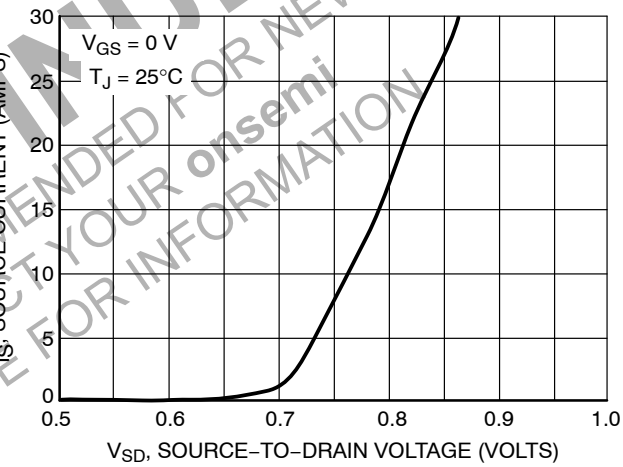


Figure 10. Diode Forward Voltage vs. Current

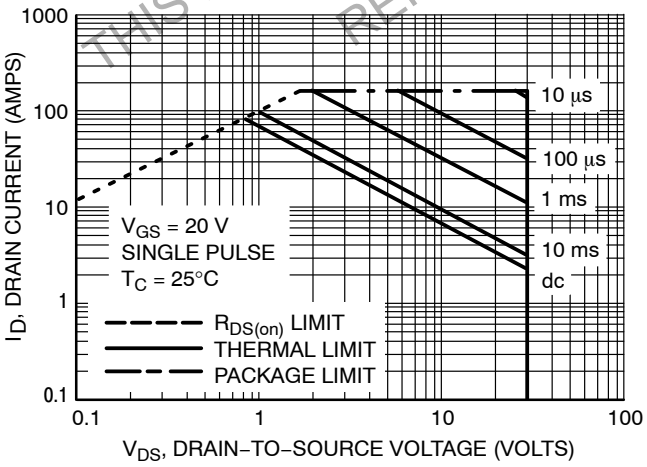


Figure 11. Maximum Rated Forward Biased Safe Operating Area

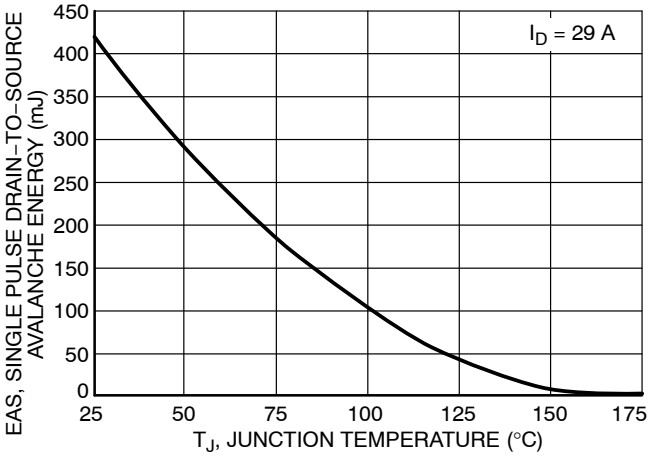


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

TYPICAL PERFORMANCE CURVES

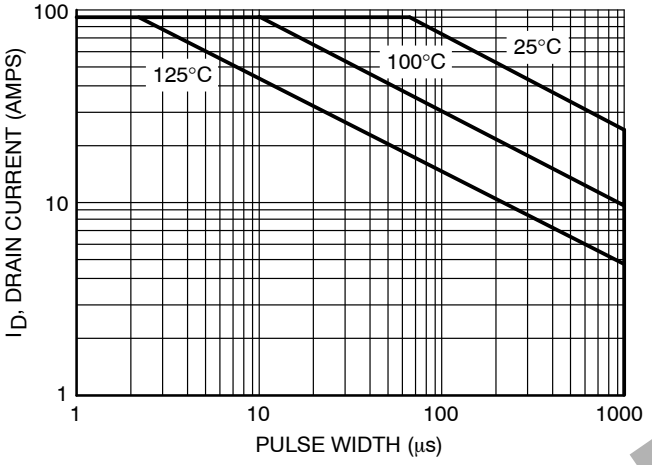


Figure 13. Avalanche Characteristics

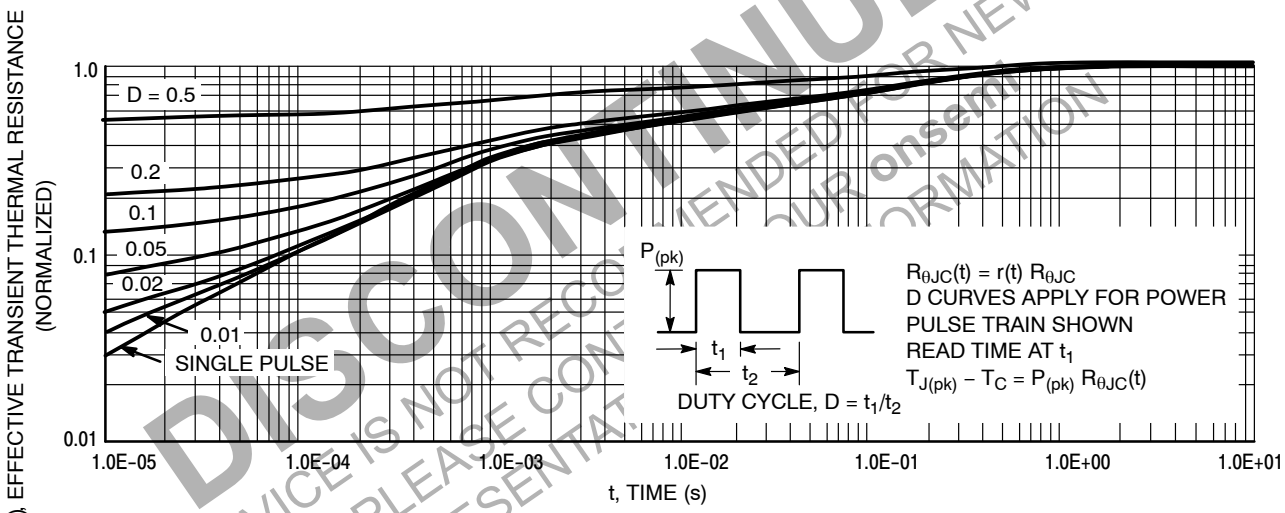


Figure 14. Thermal Response

ORDERING INFORMATION

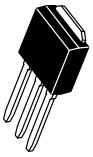
Order Number	Package	Shipping†
NTD4805NT4G	DPAK (Pb−Free)	2,500 / Tape & Reel
NTD4805N−1G	IPAK (Pb−Free)	75 Units / Rail
NVD4805NT4G*	DPAK (Pb−Free)	2,500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable.

IPAK
CASE 369D–01
ISSUE C

DATE 15 DEC 2010



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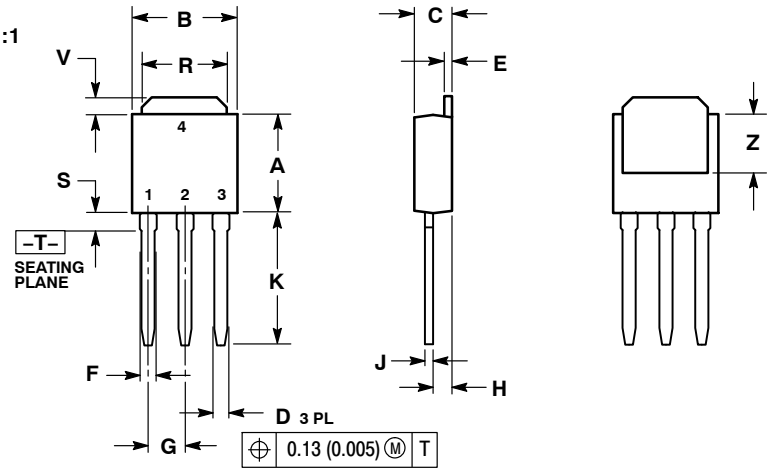


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

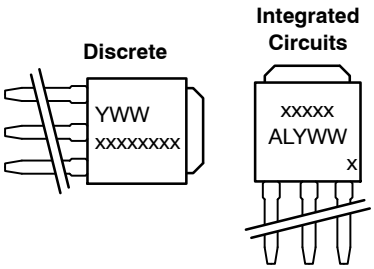
STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

MARKING DIAGRAMS

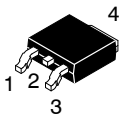


xxxxxxxxx = Device Code
A = Assembly Location
IL = Wafer Lot
Y = Year
WW = Work Week

DOCUMENT NUMBER:	98AON10528D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	IPAK (DPAK INSERTION MOUNT)	PAGE 1 OF 1

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

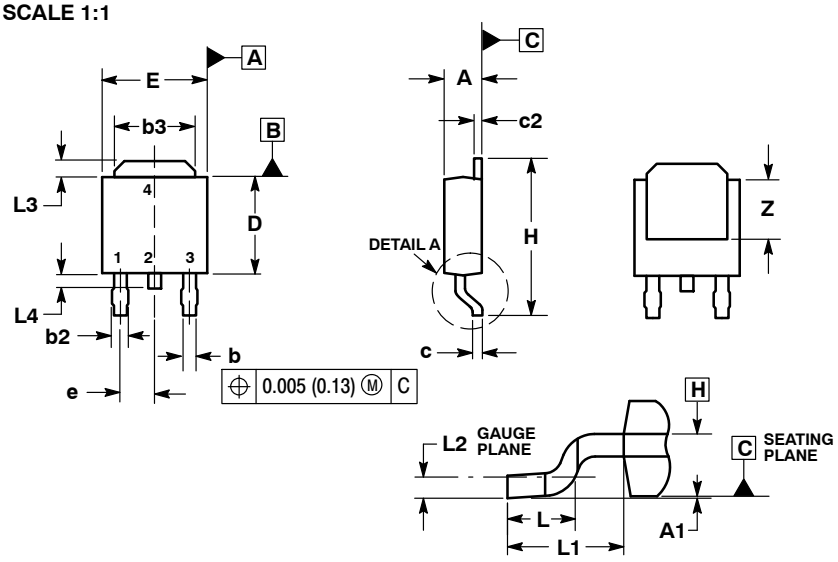
ON Semiconductor®



SCALE 1:1

DPAK (SINGLE GUAGE)
CASE 369AA−01
ISSUE B

DATE 03 JUN 2010



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	−−−	0.040	−−−	1.01
Z	0.155	−−−	3.93	−−−

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

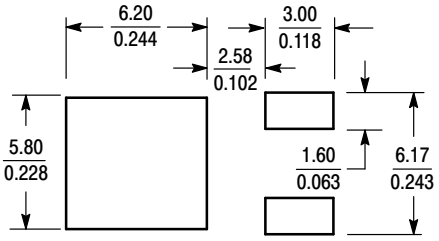
STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

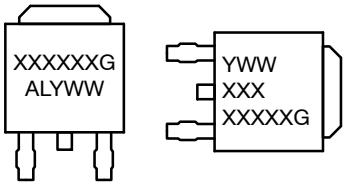
SOLDERING FOOTPRINT*



SCALE 3:1 (mm / inches)

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



IC Discrete

XXXXXX = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking.

DOCUMENT NUMBER:	98AON13126D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	DPAK (SINGLE GAUGE)	PAGE 1 OF 1

ADDITIONAL INFORMATION

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